N-Channel Enhancement Mode Power MOSFET

Description :

The KE13N50CFP is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The TO-220FP package is universally preferred for all commercial-industrial applications

Features:

- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- Insulating package, front/back side insulating voltage=2500V(AC)
- RoHS compliant package

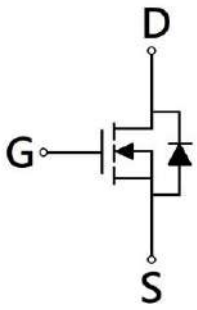
Applications:

- Power Factor Correction
- LCD TV Power
- Full and Half Bridge Power

BV_{DSS}	**500V**
I_D @V_{GS}=10V, T_C=25˚C	**13A**
I_D @V_{GS}=10V, T_C=100˚C	**8.2A**
$R_{DS(ON)}$@V_{GS}=10V, I_D=6.5A	**0.42Ω (typ)**

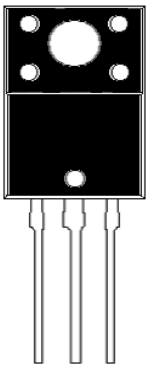
Ordering Information

Device	Package	Shipping
KE13N50CFP	TO-220FP (RoHS compliant package)	50 pcs/tube, 20 tubes/box, 5 boxes / carton



G : Gate S : Source D : Drain

TO-220FP



G D S

Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage (Note 1)	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	±30	
Continuous Drain Current @V_{GS}=10V, T_C=25°C	I_D	13*	A
Continuous Drain Current @V_{GS}=10V, T_C=100°C		8.2*	
Pulsed Drain Current @ V_{GS}=10V (Note 2)	I_{DM}	52*	
Single Pulse Avalanche Energy @ L=8mH, I_D=4Amps, V_{DD}=50V	E_{AS}	64	mJ
Single Pulse Avalanche Current (Note 2)	I_{AS}	4	A
Maximum Temperature for Soldering @ Lead at 0.063 in(1.6mm) from case for 10 seconds	T_L	300	°C
Maximum Temperature for Soldering @ Package Body for 10 seconds	T_{PKG}	260	
Total Power Dissipation (T_C=25℃)	P_D	48	W
Linear Derating Factor above 25℃		0.4	W/°C
Operating Junction and Storage Temperature	Tj, Tstg	-55~+150	°C

*Drain current limited by maximum junction temperature

*100% UIS testing in condition of V_{DD}=50V, L=8mH, V_G=10V, I_L=3A, Rated V_{DS}=500V

Note : 1. T_J=+25℃ to +150℃.

2. Pulse width limited by maximum junction temperature.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	2.58	°C/W
Thermal Resistance, Junction-to-ambient, max	$R_{\theta JA}$	62.5	

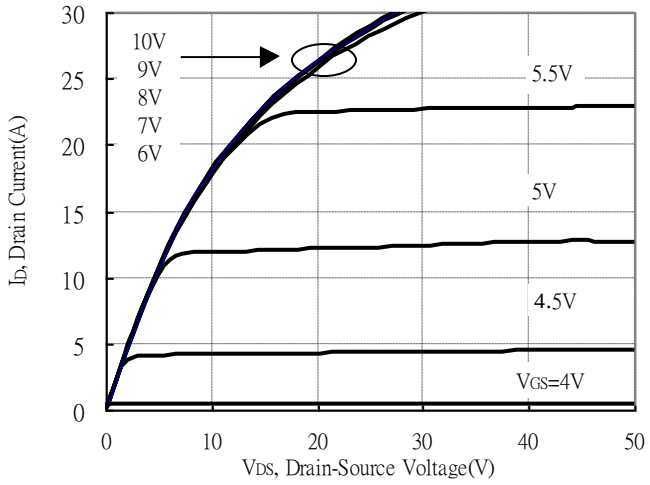
Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	500	-	-	V	V_{GS}=0V, I_D=250μA
$\Delta BV_{DSS}/\Delta Tj$	-	0.6	-	V/°C	Reference to 25°C, I_D=250μA
$V_{GS(th)}$	2.0	-	4.0	V	V_{DS} = V_{GS}, I_D=250μA
*G_{FS}	-	15	-	S	V_{DS} =15V, I_D=6.5A
I_{GSS}	-	-	±100	nA	V_{GS}=±30V
I_{DSS}	-	-	1	μA	V_{DS} =500V, V_{GS} =0V
I_{DSS}	-	-	10		V_{DS} =400V, V_{GS} =0V, Tj=125°C
*$R_{DS(ON)}$	-	0.42	0.53	Ω	V_{GS} =10V, I_D=6.5A
Dynamic					
*Qg	-	35.8	-	nC	I_D=13A, V_{DD}=250V, V_{GS}=10V
*Qgs	-	7.6	-		
*Qgd	-	10.8	-		
*$t_{d(ON)}$	-	17	-	ns	V_{DD}=250V, I_D=13A, V_{GS}=10V, R_G=9.1Ω
*tr	-	16.8	-		
*$t_{d(OFF)}$	-	63.4	-		
*t_f	-	31.8	-		
Ciss	-	1479	-	pF	V_{GS}=0V, V_{DS}=25V, f=1MHz
Coss	-	150	-		
Crss	-	36	-		
Source-Drain Diode					
*I_S	-	-	13	A	
*I_{SM}	-	-	52		
*V_{SD}	-	0.79	1.2	V	I_S=6.5A, V_{GS}=0V
*trr	-	318	-	ns	V_{GS}=0, I_F=13A, dI_F/dt=100A/μs
*Qrr	-	3.02	-	μC	

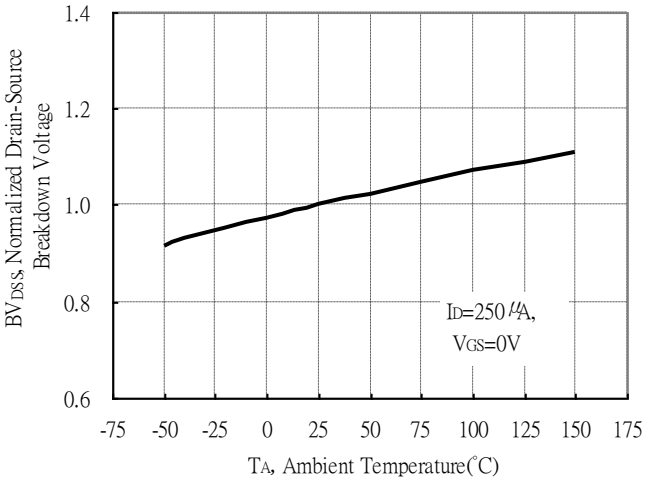
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Typical Characteristics

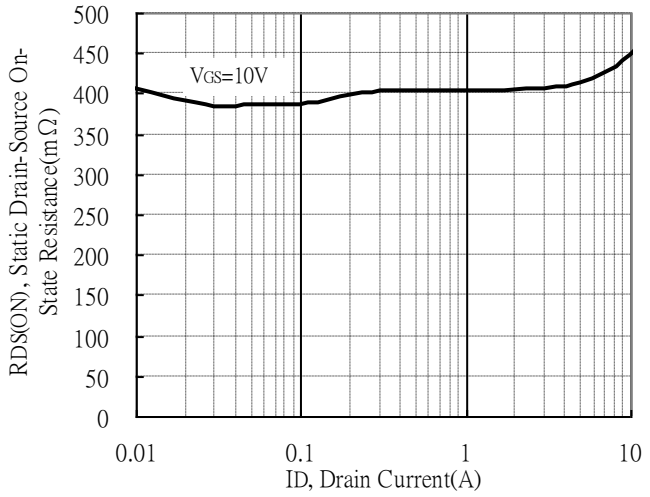
Typical Output Characteristics



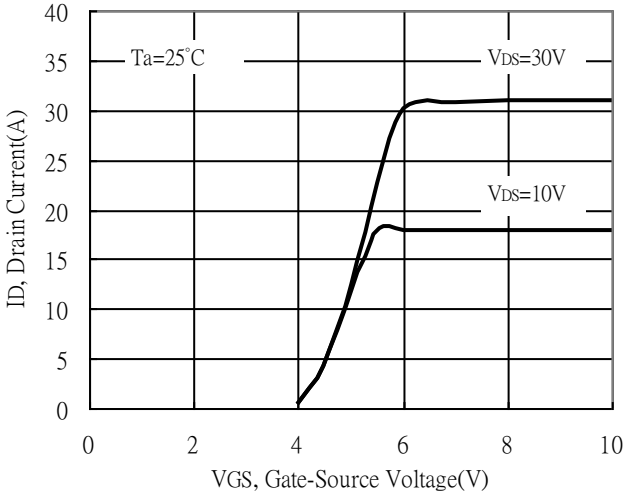
Brekdown Voltage vs Ambient Temperature



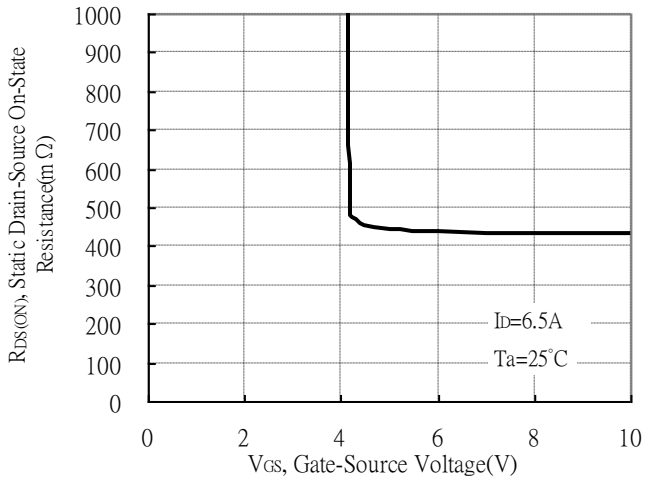
Static Drain-Source On-State resistance vs Drain Current



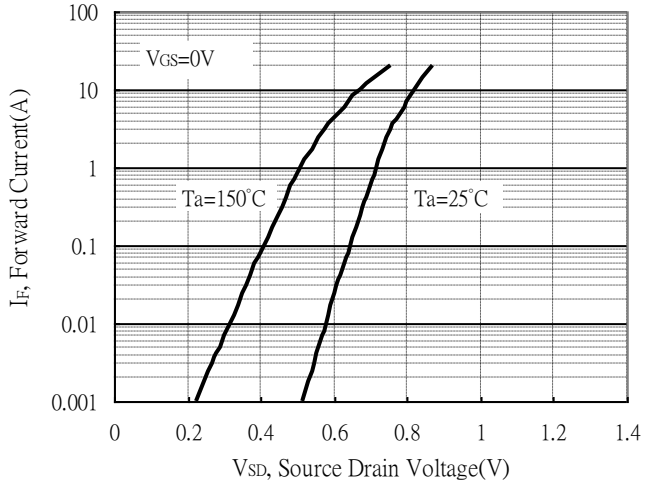
Drain Current vs Gate-Source Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

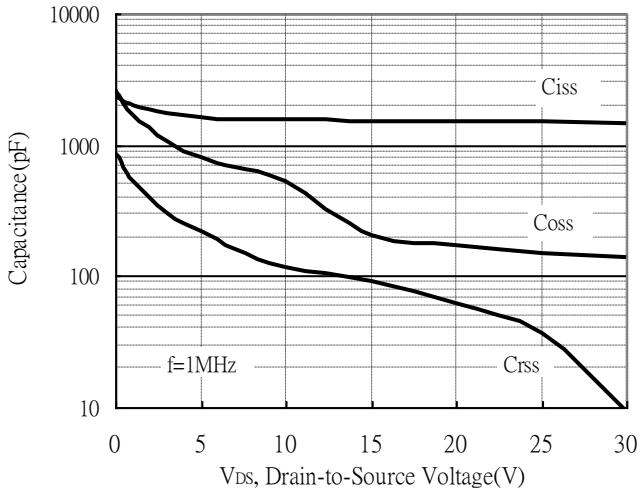


Forward Drain Current vs Source-Drain Voltage

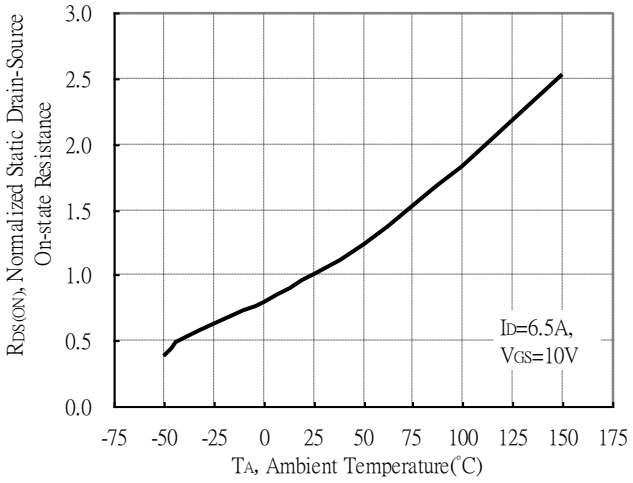


Typical Characteristics(Cont.)

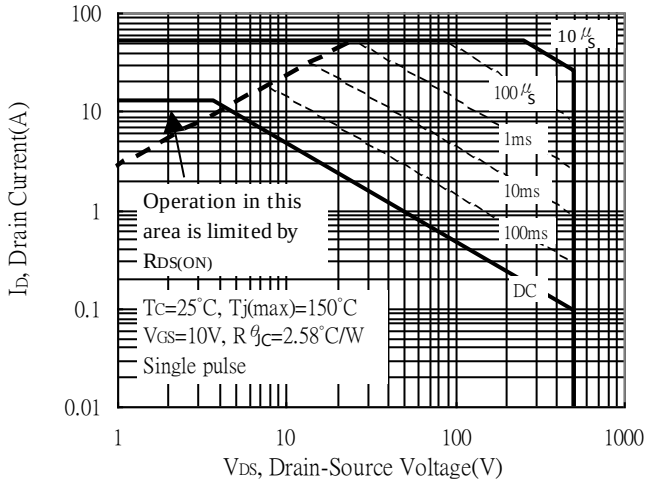
Capacitance vs Reverse Voltage



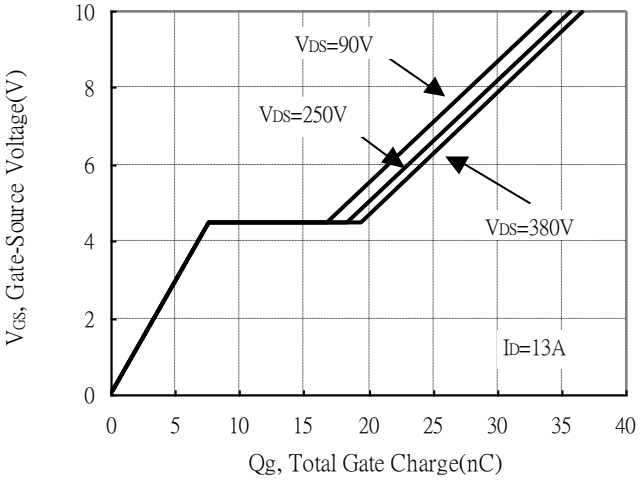
Static Drain-Source On-resistance vs Ambient Temperature



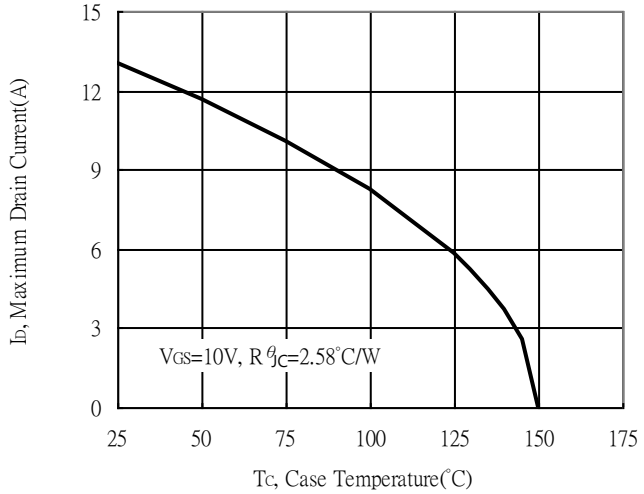
Maximum Safe Operating Area



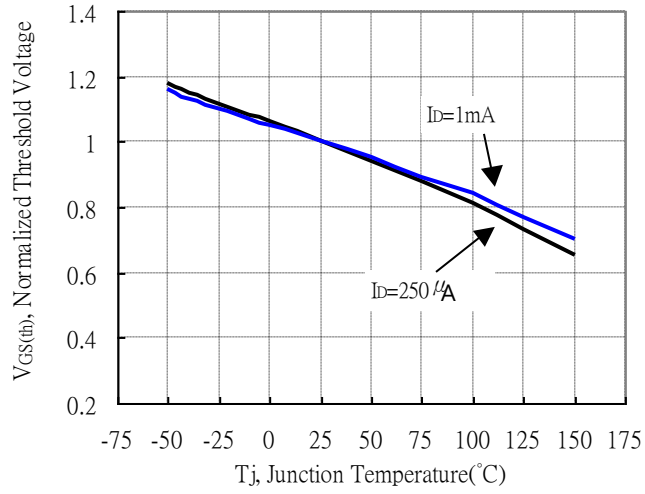
Gate Charge Characteristics



Maximum Drain Current vs Case Temperature

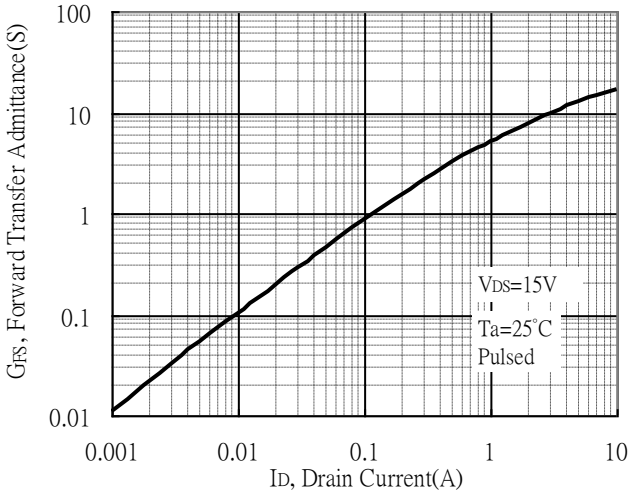


Threshold Voltage vs Junction Tempearture

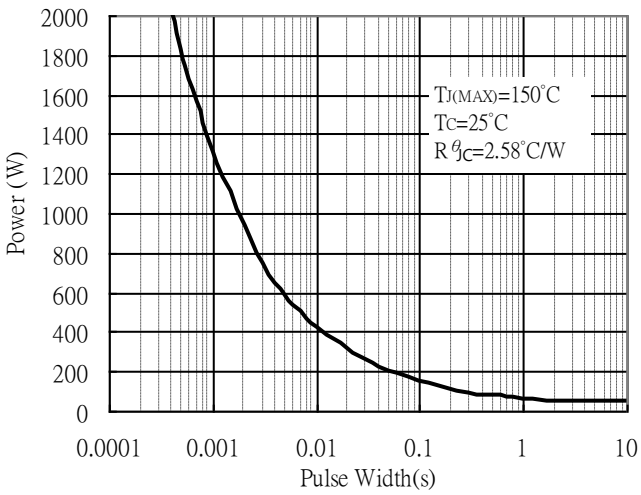


Typical Characteristics(Cont.)

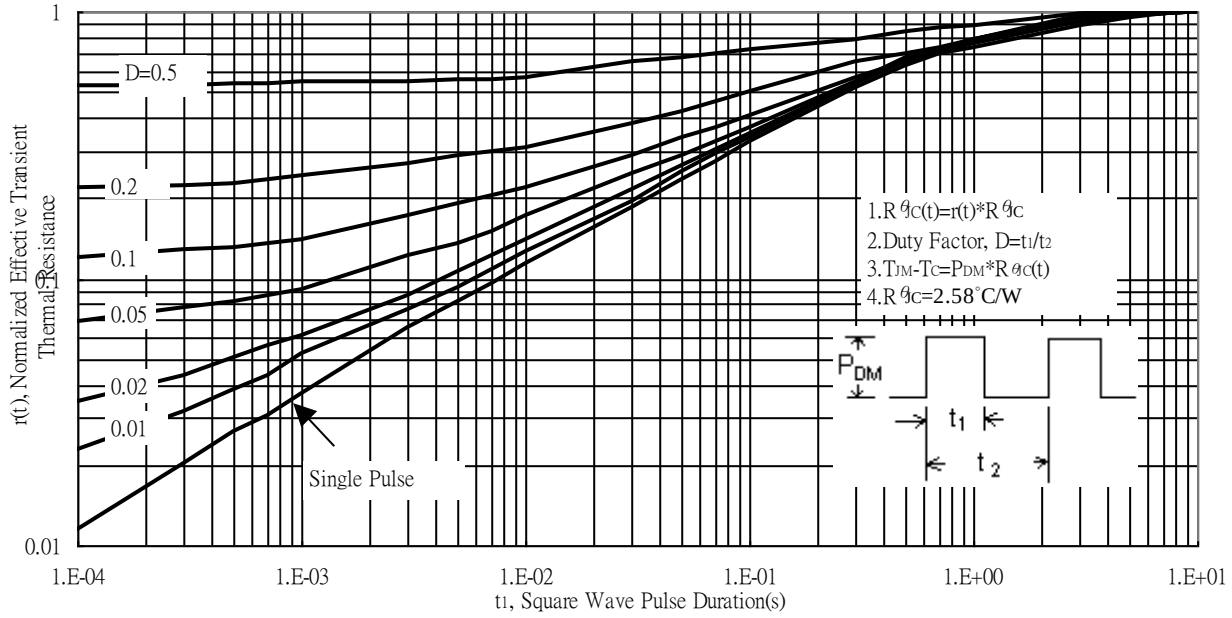
Forward Transfer Admittance vs Drain Current



Single Pulse Power Rating, Junction to Case



Transient Thermal Response Curves



Test Circuit and Waveforms

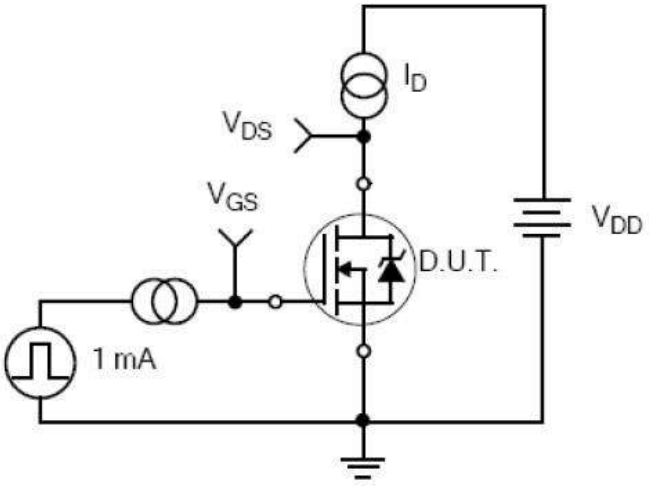


Figure 12. Gate Charge Test Circuit

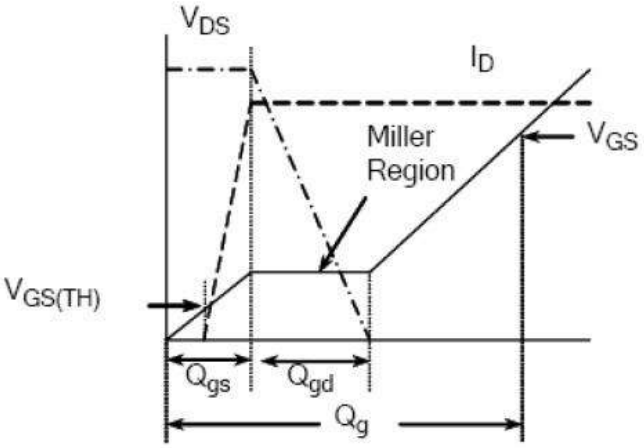


Figure 13. Gate Charge Waveform

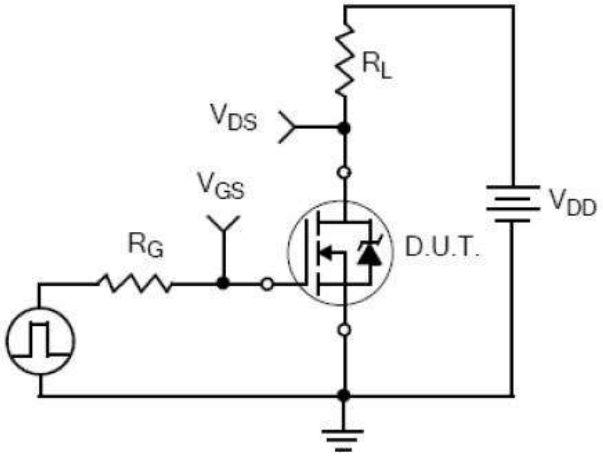


Figure 14. Resistive Switching Test Circuit

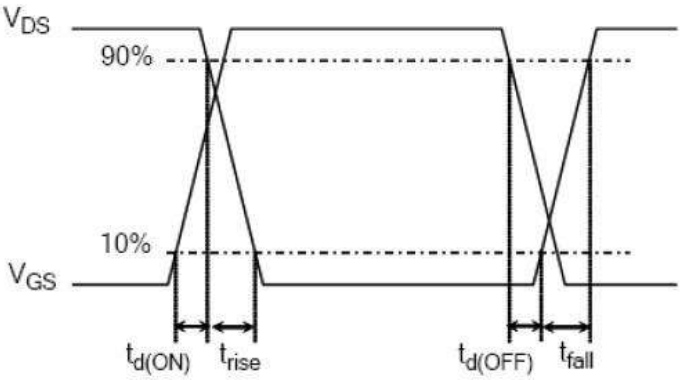


Figure 15. Resistive Switching Waveforms

Test Circuit and Waveforms(Cont.)

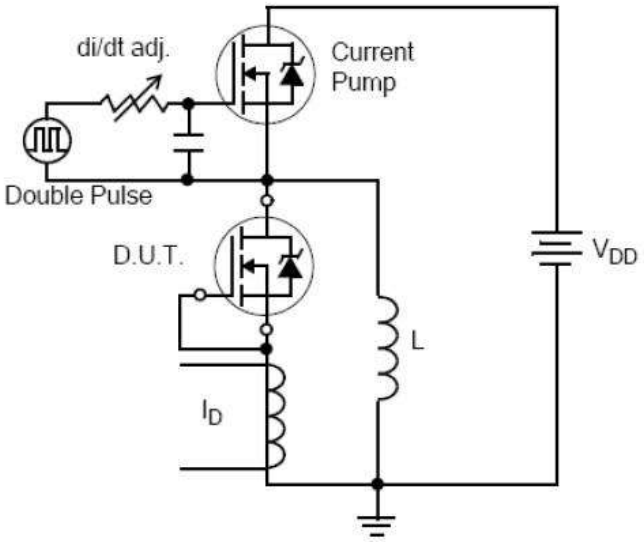


Figure 16. Diode Reverse Recovery Test Circuit

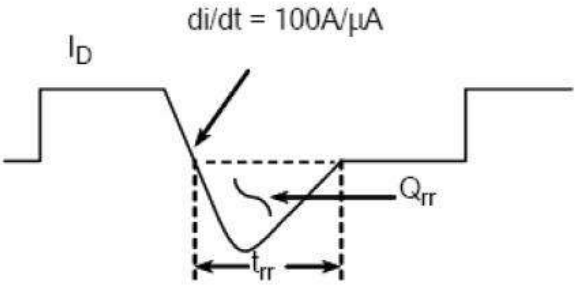


Figure 17. Diode Reverse Recovery Waveform

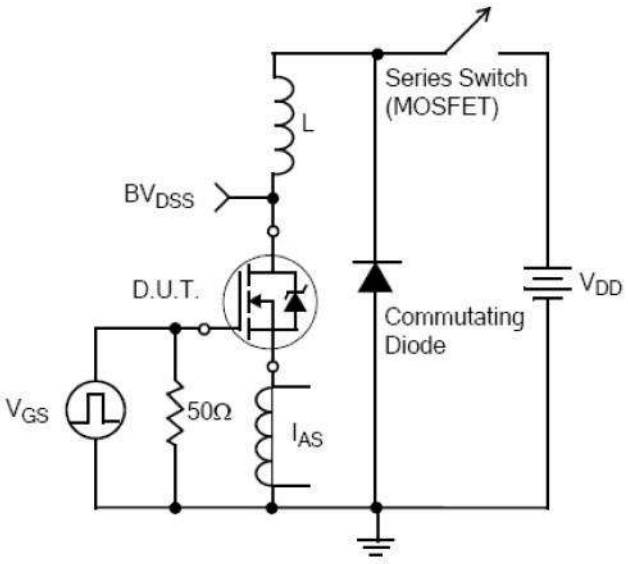


Figure 18. Unclamped Inductive Switching Test Circuit

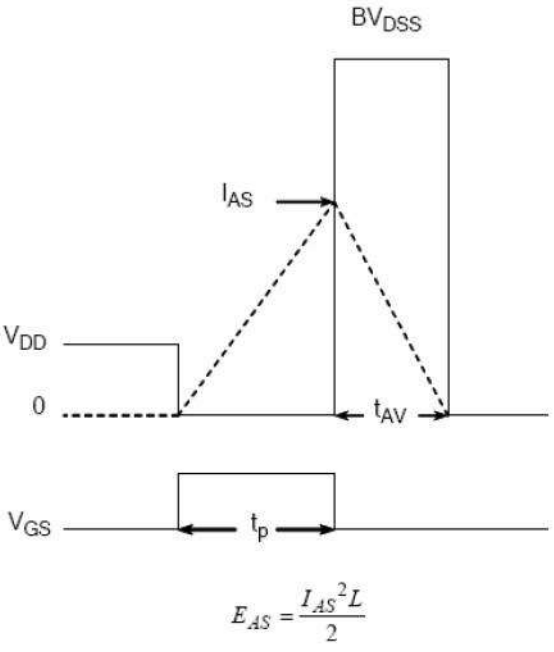
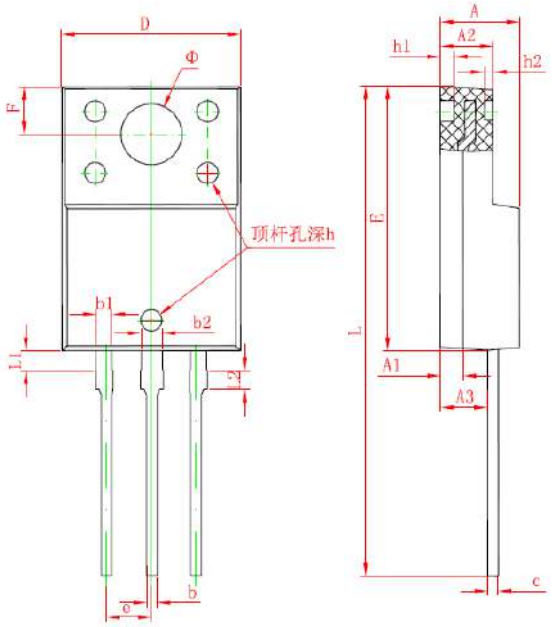


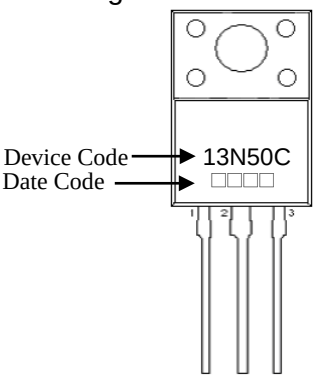
Figure 19. Unclamped Inductive Switching Waveforms

TO-220FP Dimension



3-Lead TO-220FP Plastic Package

Marking:



Style: Pin 1.Gate 2.Drain 3.Source

Date Code(counting from left to right) :
1st code: year code, the last digit of Christian year
2nd code : month code, Jan→A, Feb→B, Mar→C,
Apr→D, May→E, Jun→F, Jul→G, Aug→H,
Sep→J, Oct→K, Nov→L, Dec→M
3rd and 4th codes : production serial number, 01~99

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.169	0.185	4.35	4.65	e	0.100 TYP		2.54 TYP	
A1	0.051 REF		1.300 REF		F	0.106 REF		2.70 REF	
A2	0.112	0.124	2.85	3.15	Φ	0.138 REF		3.50 REF	
A3	0.102	0.110	2.60	2.80	h	0.000	0.012	0.00	0.30
b	0.020	0.030	0.50	0.75	h1	0.031 REF		0.80 REF	
b1	0.031	0.041	0.80	1.05	h2	0.020 REF		0.50 REF	
b2	0.043	0.053	1.10	1.35	L	1.102	1.118	28.00	28.40
c	0.020	0.030	0.50	0.75	L1	0.043	0.051	1.10	1.30
D	0.392	0.408	9.96	10.36	L2	0.036	0.043	0.92	1.08
E	0.583	0.598	14.80	15.20					